















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	TIP35C
Overseas Part Number	TIP35C
▶ Equivalent Part Number	TIP35C





TIP35C

NPN POWER TRANSISTORS

Description:

The TIP35C is a silicon Epitaxial-Base NPN power transistor mounted in TO-3P plastic package.

Features:

- Low Leakage Current
- Low Switching Loss
- Minimum Lot-to-Lot For Reliability Operation
- Low Spread Of Dynamic Parameters

Applications:

It is intented for use in power amplifier and switching applications.

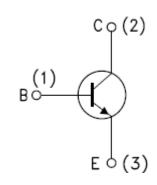
The complementary PNP type is TIP36C.

Ordering Information

PART NUMBER	PACKAGE	BRAND
TIP35C	TO-3P	EVVOSEMI

BVCEO	Ptot	Ic
140V	125W	10A





TO-3P Not to Scale

Internal Schematic Diagram

Absolute Maximum Ratings Tc= 25 °C unless otherwise specified

Samuel Demonstra		Value	TT '	
Symbol	Parameter	TIP35C	Units	
Vcbo	Collector-to-Base Voltage 140			
VCEO	Collector-to-Emitter Voltage (IB=0)	140	V	
VEBO	Emitter -to-Base Breakdown Voltage (Ic=0)	5.0		
Ic	Collector Current	10	A	
Ptot	Total Dissipation at Tamb=25°C	125	W	
T_{J}	Operation Junction	150	$^{\circ}\!\mathrm{C}$	
Тѕтс	Storage Temperature Range	-55~150		

Caution: Stresses greater than those listed in "Absolute Maximum Ratings" Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	Maximum TIP35C	Units	Test Condition
$R_{ heta JC}$	Junction-to-Case	1.0	°C/W	Water cooled heat sink, PD adjusted for a peak junction temperature of $+150^{\circ}\mathrm{C}$.
$R_{ heta JA}$	Junction-to-Case	50	°C/W	1 cubic foot chamber, free air.

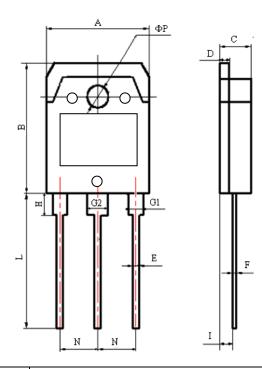


Electrical Characteristics (TJ= 25 °C unless otherwise specified):

Symbol	Parameter	Rating			Units	Test Conditions	
Symbol	yinooi i arametei		Typ.	Max.	Units	Test Conditions	
Ісво	Collector-to-Base Cut-off Current			5		Vcb=140V,IE=0A	
Ісео	Collector-to-Emitter Cut-off Current			5	uA	Vce=140V,Ie=0A	
Ієво	Emitter-to-Base Cut-off Current			5		VBE=5V,IC=0A	
Vсво	Collector-to-Base Voltage	140				Ic=0.1mA	
VCEO	Collector-to-Emitter Voltage	140			V	Ic=10mA	
VEBO	Emitter-to-Base Voltage	5				IE=5mA	
hfE	DC Current Gain (Common Emitter)	55		160		Vce=5V,Ic=1A *	
hfE1	DC Current Gain (Common Emitter)	35				Vce=5V,Ic=5A	
VCESAT	Collector-to-Emitter Saturation Voltage			2.0	37	Ic=7A,I _B =0.7A *	
VBESAT	Base-to-Emitter Saturation Voltage			1.5	V	Vce=5V,Ic=5A	
fT	Characteristic Frequency		30		MHz	Vce=5V,Ic=1A, f=1MHz	



TO-3P MECHANICAL DATA



DIM.	mm			
Divi.	MIN	MAX		
A	15.10	15.90		
В	19.30	20.30		
С	4.70	4.90		
D	1.40	1.60		
Е	0.90	1.10		
F	0.50	0.70		
G1	2.00	2.20		
G2	3.00	3.20		
Н	3.00	3.60		
I	1.20	1.60		
L	19.00	21.00		
N	5.25	5.65		
фР	3.10	3.30		



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